



# THE DATASHEET OF STFI7N80K5



## N-channel 800 V, 0.95 $\Omega$ typ., 6 A MDmesh™ K5 Power MOSFETs in TO-220FP and I<sup>2</sup>PAKFP packages

Datasheet - production data

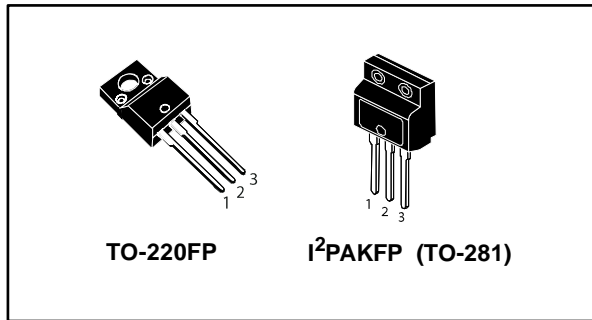
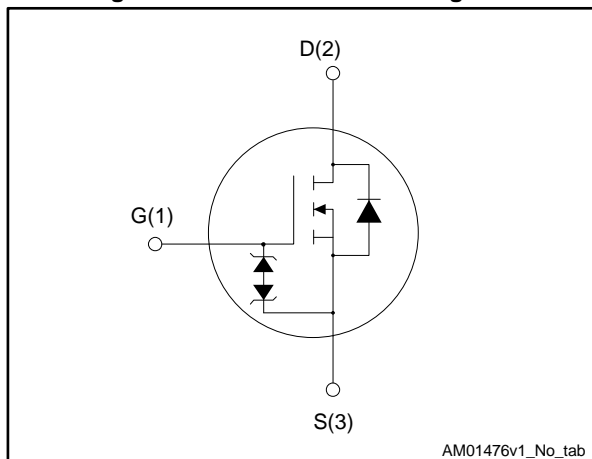


Figure 1: Internal schematic diagram



AM01476v1\_No\_tab

### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>	P <sub>TOT</sub>
STF7N80K5	800 V	1.2 $\Omega$	6 A	25 W
STFI7N80K5				

- Industry's lowest R<sub>DS(on)</sub> x area
- Industry's best FoM (figure of merit)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications

### Description

These very high voltage N-channel Power MOSFETs are designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1: Device summary

Order code	Marking	Package	Packing
STF7N80K5	7N80K5	TO-220FP	Tube
STFI7N80K5		I <sup>2</sup> PAKFP (TO-281)	

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 30$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	6	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	3.8	A
$I_{DM}^{(2)}$	Drain current (pulsed)	24	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	25	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	4.5	V/ns
$dv/dt^{(4)}$	MOSFET $dv/dt$ ruggedness	50	
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t=1\text{ s}$ ; $T_C=25\text{ }^\circ\text{C}$ )	2500	V
$T_j$	Operating junction temperature range	- 55 to 150	$^\circ\text{C}$
$T_{stg}$	Storage temperature range		

**Notes:**

(1)Limited by package.

(2)Pulse width limited by safe operating area

(3) $I_{SD} \leq 6\text{ A}$ ,  $di/dt \leq 100\text{ A}/\mu\text{s}$ ,  $V_{DS(peak)} \leq V_{(BR)DSS}$

(4) $V_{DS} \leq 640\text{ V}$

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	5	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	$^\circ\text{C}/\text{W}$

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$ )	2	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	88	mJ

## 2 Electrical characteristics

$T_C = 25\text{ °C}$  unless otherwise specified

**Table 5: On/off-state**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	800			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 800\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 800\text{ V}$ $T_C = 125\text{ °C}$ <sup>(1)</sup>			50	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DD} = V_{GS}$ , $I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 3\text{ A}$		0.95	1.2	$\Omega$

**Notes:**

<sup>(1)</sup>Defined by design, not subject to production test.

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	360	-	pF
$C_{oss}$	Output capacitance		-	30	-	pF
$C_{rss}$	Reverse transfer capacitance		-	1	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }640\text{ V}$ , $V_{GS} = 0\text{ V}$	-	47	-	pf
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	20	-	pf
$R_g$	Intrinsic gate resistance	$f = 1\text{ MHz}$ , $I_D = 0\text{ A}$	-	6	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 640\text{ V}$ , $I_D = 6\text{ A}$ $V_{GS} = 0\text{ to }10\text{ V}$ (see <a href="#">Figure 16: "Test circuit for gate charge behavior"</a> )	-	13.4	-	nC
$Q_{gs}$	Gate-source charge		-	3.7	-	nC
$Q_{gd}$	Gate-drain charge		-	7.5	-	nC

**Notes:**

<sup>(1)</sup> $C_{o(tr)}$  is a constant capacitance value that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

<sup>(2)</sup> $C_{o(er)}$  is a constant capacitance value that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$ , $I_D = 3\text{ A}$ , $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 15: "Test circuit for resistive load switching times"</a> and <a href="#">Figure 20: "Switching time waveform"</a> )	-	11.3	-	ns
$t_r$	Rise time		-	8.3	-	ns
$t_{d(off)}$	Turn-off delay time		-	23.7	-	ns
$t_f$	Fall time		-	20.2	-	ns

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		6	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		24	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 6\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 6\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ (see <a href="#">Figure 17: "Test circuit for inductive load switching and diode recovery times"</a> )	-	315		ns
$Q_{rr}$	Reverse recovery charge		-	2.8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	17.5		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 6\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ (see <a href="#">Figure 17: "Test circuit for inductive load switching and diode recovery times"</a> )	-	480		ns
$Q_{rr}$	Reverse recovery charge		-	3.8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	16		A

**Notes:**

(1)Pulse width limited by safe operating area

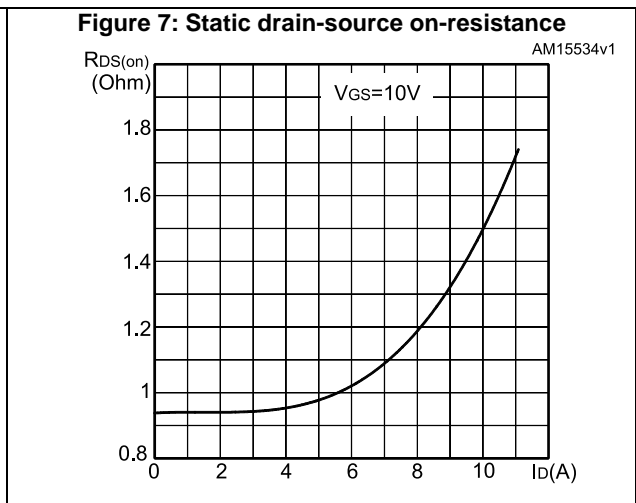
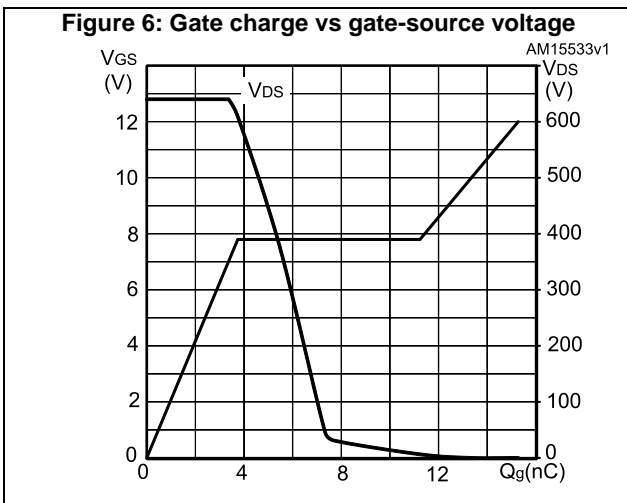
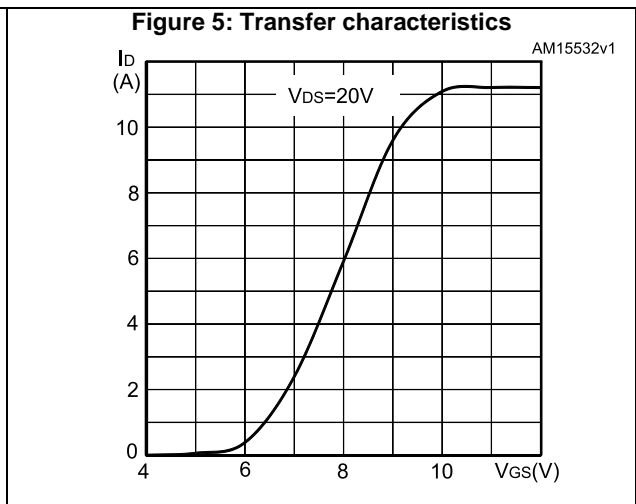
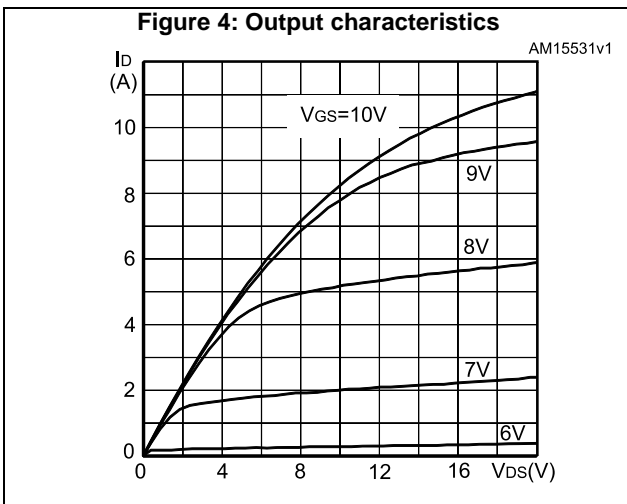
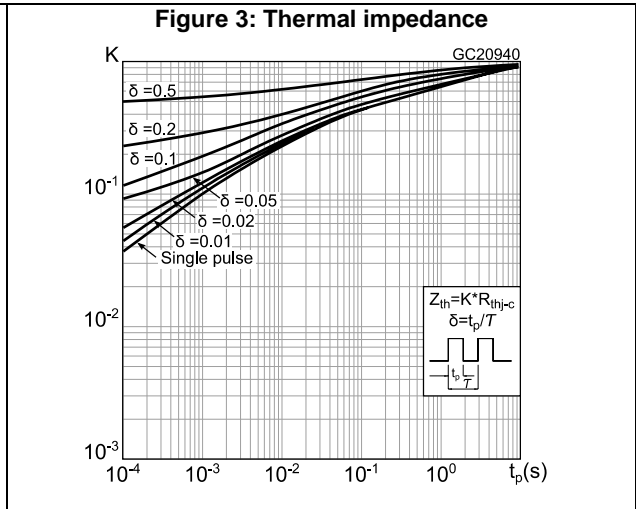
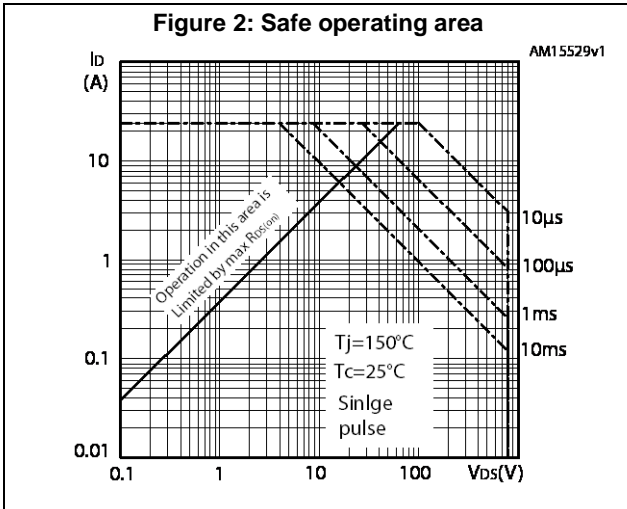
(2)Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ , $I_D = 0\text{ A}$	$\pm 30$	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

## 2.1 Electrical characteristics (curves)



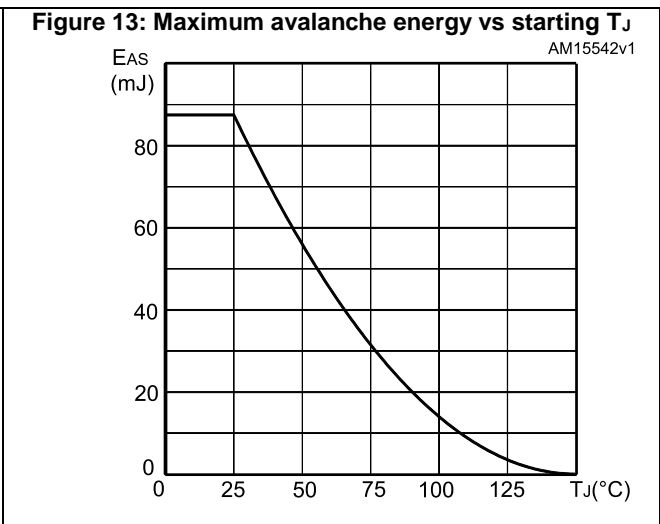
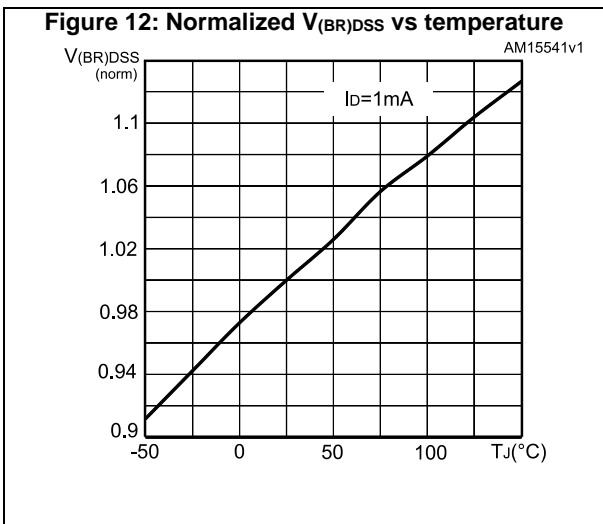
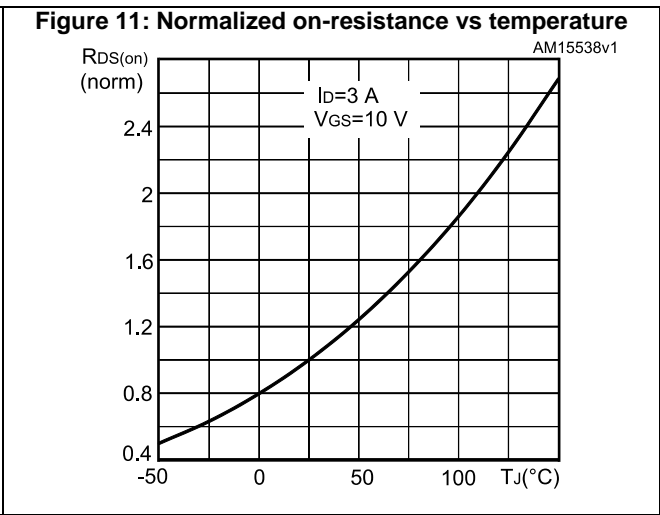
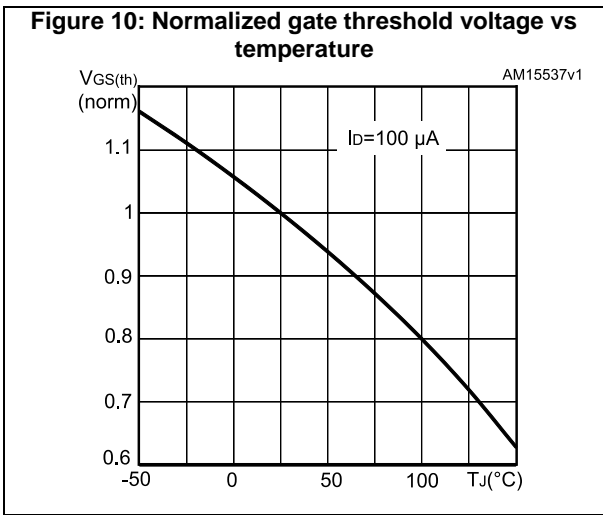
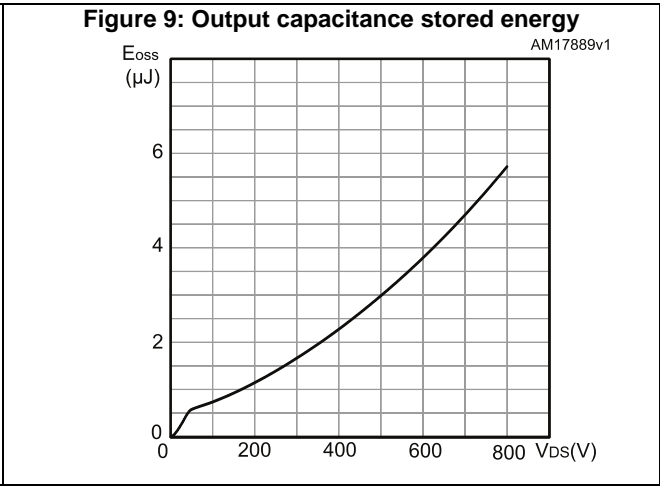
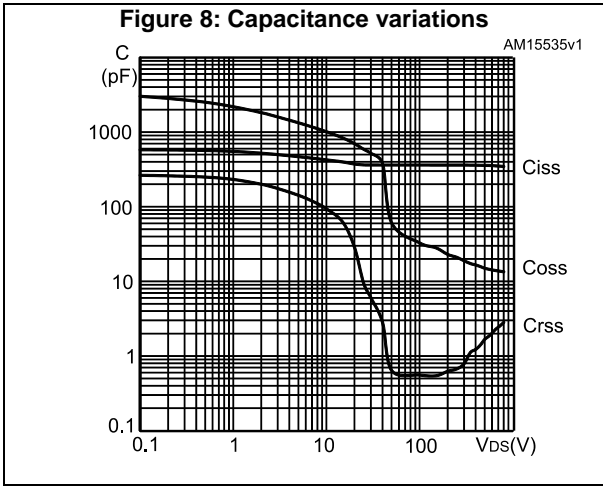
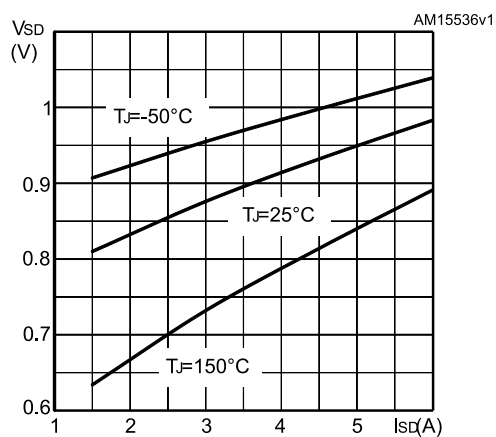
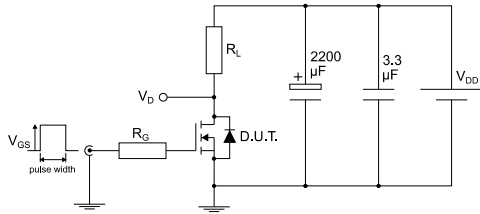


Figure 14: Source-drain diode forward characteristics



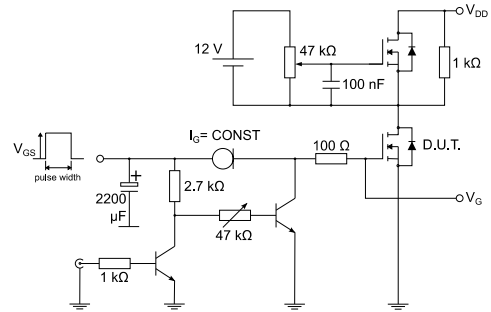
### 3 Test circuits

**Figure 15: Test circuit for resistive load switching times**



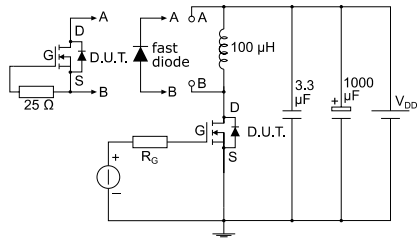
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**Figure 16: Test circuit for gate charge behavior**



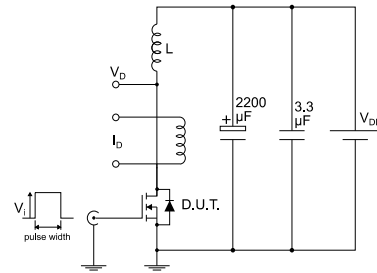
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**Figure 17: Test circuit for inductive load switching and diode recovery times**



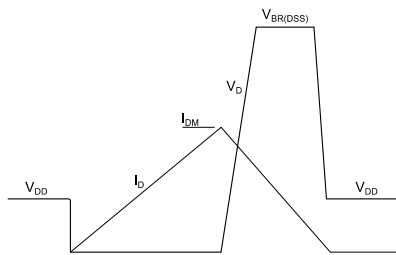
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**Figure 18: Unclamped inductive load test circuit**



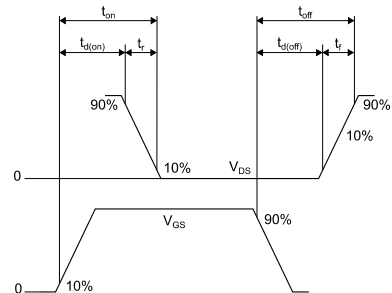
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**Figure 19: Unclamped inductive waveform**



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**Figure 20: Switching time waveform**



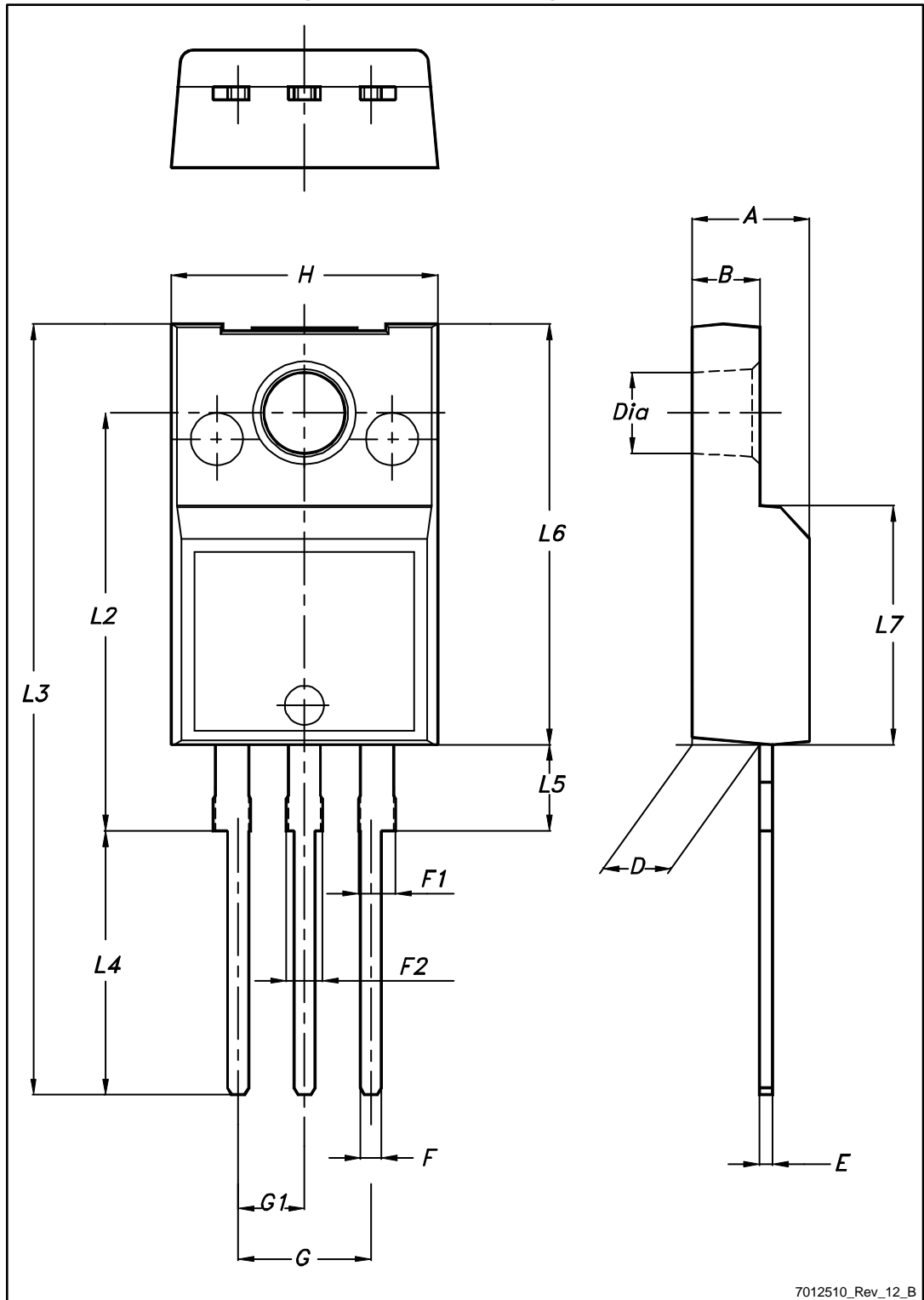
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## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 TO-220FP package information

Figure 21: TO-220FP package outline



7012510\_Rev\_12\_B

Table 10: TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

### 4.2 I<sup>2</sup>PAKFP (TO-281) package information

Figure 22: I<sup>2</sup>PAKFP (TO-281) package outline

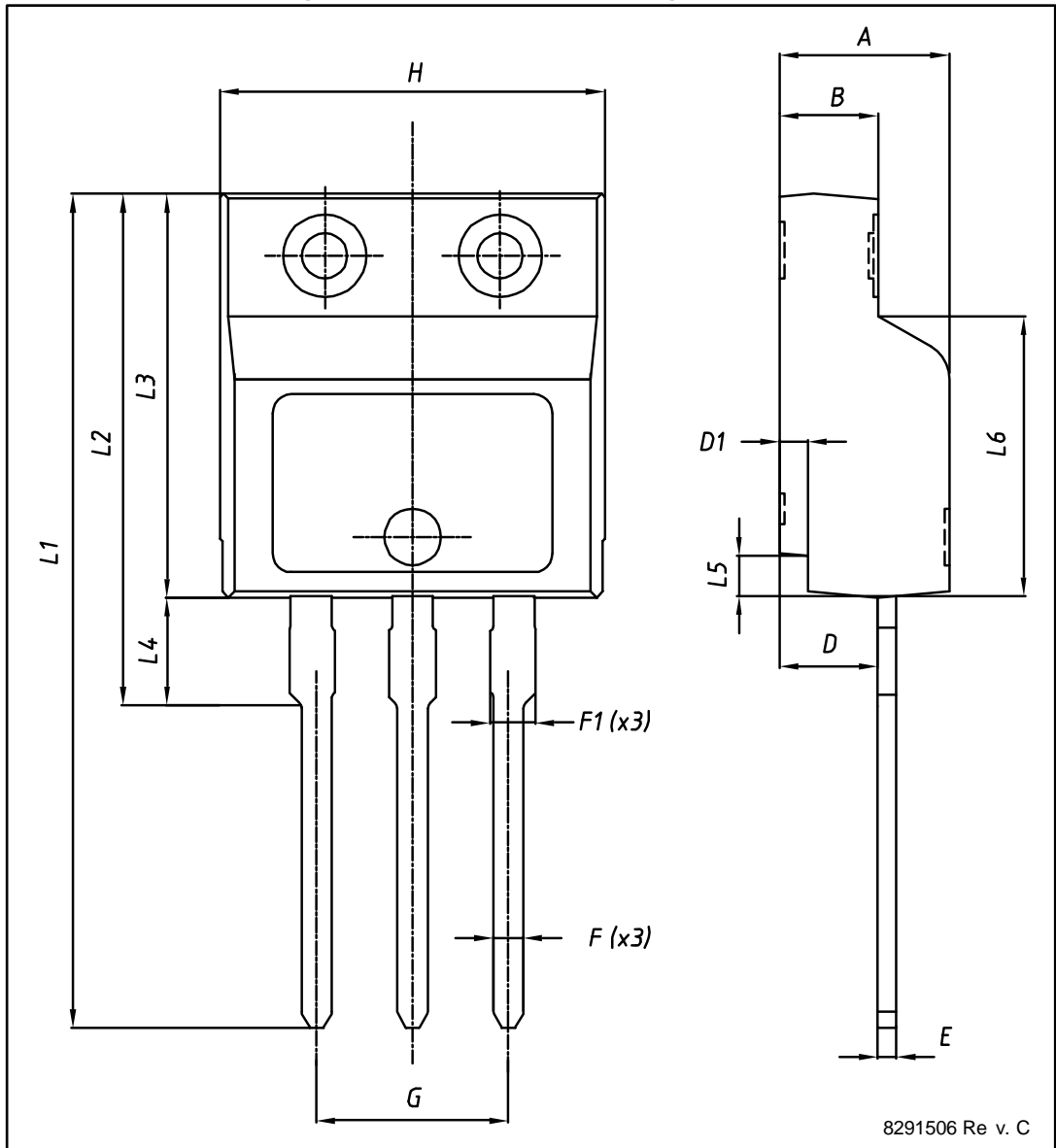


Table 11: I<sup>2</sup>PAKFP (TO-281) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95		5.20
H	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25
L6	7.50	7.60	7.70

## 5 Revision history

**Table 12: Document revision history**

Date	Revision	Changes
11-Oct-2013	1	First release. Part numbers previously included in datasheet DocID023448
05-Jul-2017	2	Modified features on cover page. Modified <a href="#">Table 2: "Absolute maximum ratings"</a> , <a href="#">Table 7: "Switching times"</a> and <a href="#">Table 9: "Gate-source Zener diode"</a> . Minor text changes.

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